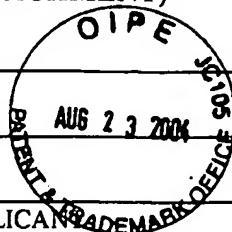


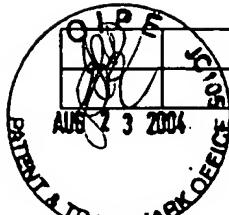
Section 2. Form PTO - 1449 (Modified) (ATTACHMENT)



FORM PTO-1449 U.S. DEPT. OF COMMERCE (Modified) PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. QIL-1CDV	SERIAL NO. 10/763,461
	APPLICANT Shchukin et al.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	FILING DATE 1/23/04	GROUP 2811

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Exam Initial	DOCUMENT NUMBER	DATE	PATENTEE	CLASS	SUB	FILING DATE IF APPROPR
Q	4,806,996	02/21/89	Luryi, S.	357	16	02/25/1988
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FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

Exam Initial	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB	TRANSLATION YES NO

OTHER PRIOR ART

Exam Initial	Author, Title, Date, Pertinent Pages, Etc
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Section 2. Form PTO - 1449 (Modified) (ATTACHMENT)

FORM PTO-1449 U.S. DEPT. OF COMMERCE (Modified) PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. NSC-QIL1CDV	SERIAL NO. 10/763,461
		APPLICANT Shchukin et al.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		FILING DATE January 23, 2004	GROUP 2815

AUG 18 2005

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FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

Exam Initial	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB	TRANSLATION YES NO
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OTHER PRIOR ART

Exam Initial	Author, Title, Date, Pertinent Pages, Etc
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<i>Julie Maldonado</i>	12/07/2005

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leung maldonado	12/07/2005